

TL0375J 2.0 – 5.0 GHz GaAs Ultra Low Noise Amplifier

Application Note: TL0375J EVB B

Application Note 3700MHz~4200MHz 5.0V 60mA

Rev-1.1

Revision 1.1, 2023-11-08

Tagore Technology

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1. General Description

The TL0375J is a broadband, ultra-low Noise Amplifier (LNA) providing high gain and linearity. With a simple input and output match, this LNA can be tuned for different frequency bands targeting LTE (small cells and infrastructure) and any other applications requiring low noise, high gain, and linearity. For <3GHz frequency band, TL0374J can be considered. The TL0375J is packaged in a compact, low-cost Dual Flat No Lead (DFN) 2x2x0.75mm, 8 pin plastic package.

TL0375J-EVB-B is an evaluation board specially tuned for frequency range of 3700MHz~4200MHz applications. Its high gain, low noise performance makes it suitable for application of public safety, radar, tactical radio, IoT, Cellular infrastructure, LTE etc.

2. TL0375J-EVB-B Board Details

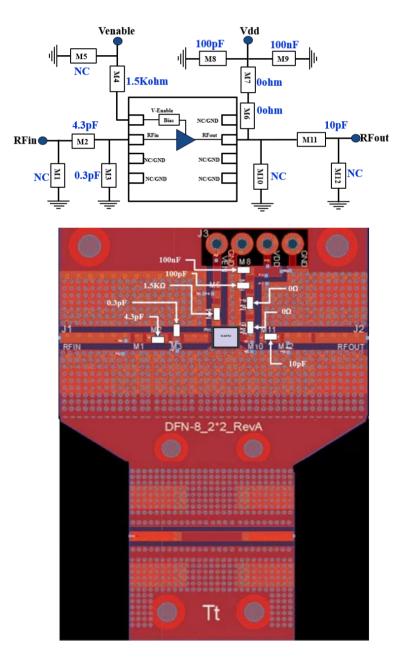


Figure 2.1 TL0375J-EVB-B 3700MHz ~ 4200MHz Schematic and EVB Layout



3. TL0375J-EVB-B Bill of Material

Component ID	Value	Manufacturer Recommended Part Num		
M2	4.3pF	Murata	GJM1555C1H4R3BB01	
M3	0.3pF	Murata	GJM1555C1HR30BB01	
M4	1.5ΚΩ	Panasonic	ERJ-2RKF1501X	
M8	100pF	AVX	04025A101JAT4A	
M9	100nF	TDK	C1005X7R1H104K050BE	
M7	0Ω	Panasonic	ERJ-2GE0R00X	
M6	0Ω	Panasonic	ERJ-2GE0R00X	
M11	10pF	AVX	04025A100JAT4A	
Q1	GaAs LNA	Tagore Technology	TL0375J	
PCB		Rogers RO4350B, 20 mils, 1 oz copper		

Table 3.1 TL0375J-EVB-B BOM

4. TL0375J-EVB-B Biasing Sequence

Turn ON Device	Turn OFF Device		
1. Set Venable to +5V	1. Turn RF power off		
2. Set V _{DD} to +5V	2. Turn off V _{DD}		
3. Device will draw required I _{DQ} current	3. Turn off Venable		
4. Apply RF power			

Table 4.1 TL0375J-EVB-B Bias and Sequencing

5. TL0375J-EVB-B Board Measurement Summary

Frequency (MHz)	EVB Noise Figure (dB)	Gain (dB)	OP1 (dBm)	OIP3(dBm) Fspacing:1MHz 0dBm Pout/tone	S11 (dB)	S22 (dB)	Mu1
3700	0.6	17.0	20.4	34.3	-15.4	-7.8	1.2
3800	0.6	16.8	20.7	34.0	-15.2	-8.5	1.3
3900	0.6	16.6	20.3	34.2	-14.8	-8.8	1.3
4000	0.6	16.6	20.3	34.1	-14.3	-9.1	1.3
4100	0.7	16.5	20.2	34.1	-14.0	-8.8	1.2
4200	0.7	16.4	20.1	34.1	-13.8	-8.9	1.2

Table 5.1 TL0375J-EVB-B Electrical Characteristics Summary



6. TL0375J-EVB-B Test Results

All the tests are carried out at room temperature.

6.1. S parameters

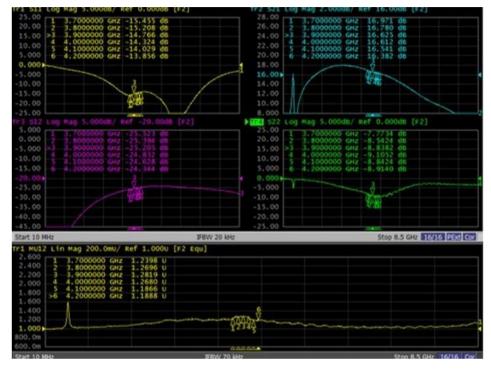
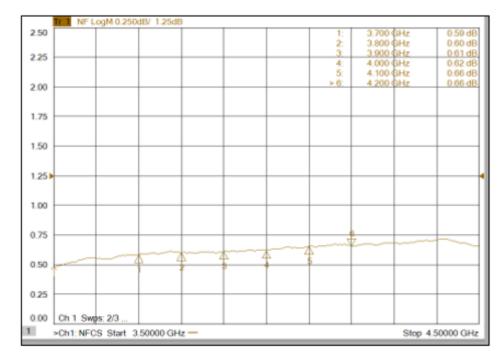


Figure 6.1.1. S parameters of TL0375J-EVB-B

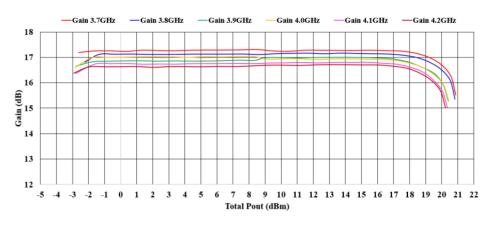


6.2. EVB Noise Figure

Figure 6.2.1. EVB Noise Figure mode of TL0375J-EVB-B



6.3. Large Signal Test Results





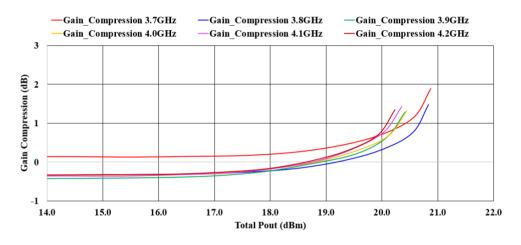


Figure 6.3.2. Gain compression Vs Pout of TL0375J-EVB-B

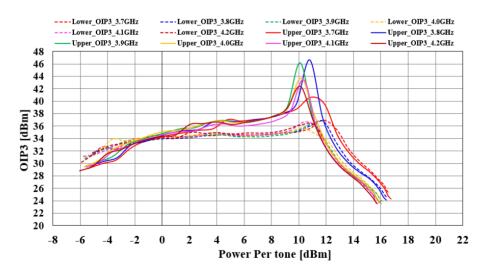


Figure 6.3.3. Output 3rd Order Intercept Point of TL0375J-EVB-B



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